

Product Overview

NTTFS4C06N: Single N-Channel Power MOSFET 30V, 65A, 4.2mΩ

For complete documentation, see the data sheet.

Power MOSFET
30 V, 67 A, Single N-Channel, μ8FL

Features

- Low RDS(on) to Minimize Conduction Losses
- Low Capacitance to Minimize Driver Losses
- Optimized Gate Charge to Minimize Switching Losses
- RoHS Compliant

Benefits

- Improve System Efficiency
- Improve System Efficiency

Applications

- DC-DC Converters
- Power Load Switch
- Notebook Battery Management

Part Electrical Specifications

Product	Pricing (\$/Unit)	Compliance	Status	Channel Polarity	Configuration	V _{DS(BR)} Min (V)	V _{GS} Max (V)	V _{GS(th)} Max (V)	I _D Max (A)	P _D Max (W)	R _{DS(on)} Max @ V _{GS} = 2.5 V (mΩ)	R _{DS(on)} Max @ V _{GS} = 4.5 V (mΩ)	R _{DS(on)} Max @ V _{GS} = 10 V (mΩ)	Q _g Typ @ V _{GS} = 4.5 V (nC)	Q _g Typ @ V _{GS} = 10 V (nC)	C _{iss} Typ (pF)	Package Type
NTTFS4C06NTAG	0.2973	Pb-free Halide free	Active	N-Channel	Single	30	20	2.2	67	31	-	6.1	4.2	-	4	1683	WDF N-8 / u8FL
NTTFS4C06NTWG	0.2973	Pb-free Halide free	Active	N-Channel	Single	30	20	2.2	67	31	-	6.1	4.2	-	4	1683	WDF N-8 / u8FL

For more information please contact your local sales support at www.onsemi.com.

Created on: 7/8/2020